



August 2014

FDPF33N25T

N-Channel UniFET™ MOSFET

250 V, 33 A, 94 mΩ

Features

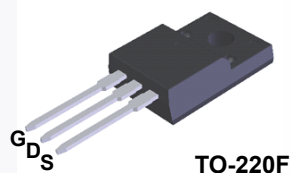
- $R_{DS(on)} = 94 \text{ m}\Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$, $I_D = 16.5 \text{ A}$
- Low Gate Charge (Typ. 36.8 nC)
- Low C_{RSS} (Typ. 39 pF)
- 100% Avalanche Tested

Applications

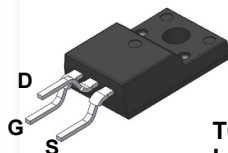
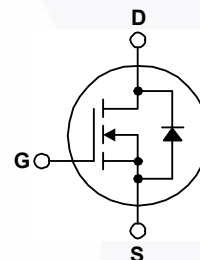
- PDP TV
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

Description

UniFET™ MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



TO-220F

TO-220F
LG-formed

Absolute Maximum Ratings

 $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter		FDPF33N25T FDPF33N25TRDTU	Unit
V_{DSS}	Drain-Source Voltage		250	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	33*	A
		- Continuous ($T_C = 100^\circ\text{C}$)	20.4*	A
I_{DM}	Drain Current	- Pulsed (Note 1)	132*	A
V_{GSS}	Gate-Source voltage		± 30	V
E_{AS}	Single Pulsed Avalanche Energy		918	mJ
I_{AR}	Avalanche Current		33	A
E_{AR}	Repetitive Avalanche Energy		23.5	mJ
dv/dt	Peak Diode Recovery dv/dt		4.5	V/ns
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	37	W
		- Derate Above 25°C	0.29	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	$^\circ\text{C}$

*Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FDPF33N25T FDPF33N25TRDTU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	3.4	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDPF33N25T	FDPF33N25T	TO-220F	Tube	N/A	N/A	50 units
FDPF33N25TRDTU	FDPF33N25T	TO-220F (LG-formed)	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA, T _J = 25°C	250	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.25	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 250 V, V _{GS} = 0 V V _{DS} = 200 V, T _C = 125°C	-- --	-- --	1 10	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3.0	--	5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 16.5 A	--	0.077	0.094	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 16.5 A	--	26.6	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	1640	2135	pF
C _{oss}	Output Capacitance		--	330	430	pF
C _{rss}	Reverse Transfer Capacitance		--	39	59	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 125 V, I _D = 33 A, V _{GS} = 10 V, R _G = 25 Ω (Note 4)	--	35	80	ns
t _r	Turn-On Rise Time		--	230	470	ns
t _{d(off)}	Turn-Off Delay Time		--	75	160	ns
t _f	Turn-Off Fall Time		--	120	250	ns
Q _g	Total Gate Charge	V _{DS} = 200 V, I _D = 33 A, V _{GS} = 10 V (Note 4)	--	36.8	48	nC
Q _{gs}	Gate-Source Charge		--	10	--	nC
Q _{gd}	Gate-Drain Charge		--	17	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	33	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	132	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 33 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 33 A, dI _F /dt = 100 A/μs	--	220	--	ns
Q _{rr}	Reverse Recovery Charge		--	1.71	--	μC

Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. $L = 1.35\text{ mH}, I_{AS} = 33\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\text{ }\Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 33\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

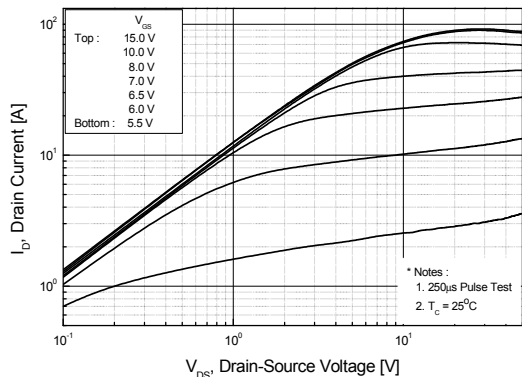


Figure 2. Transfer Characteristics

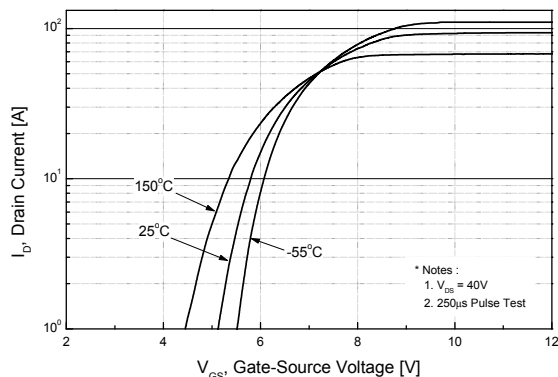


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

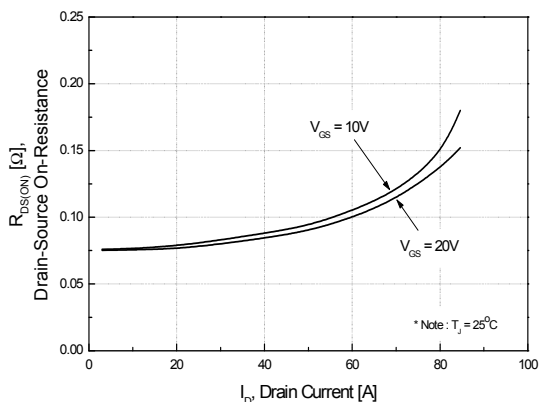


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

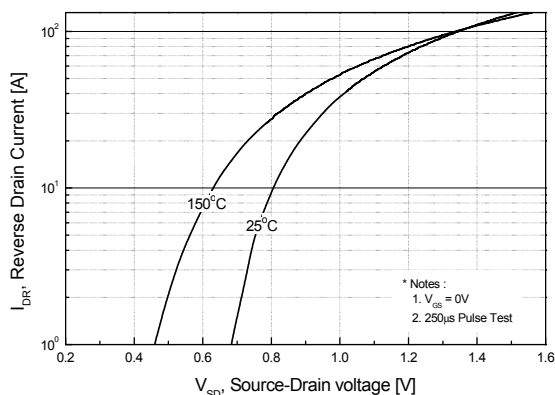


Figure 5. Capacitance Characteristics

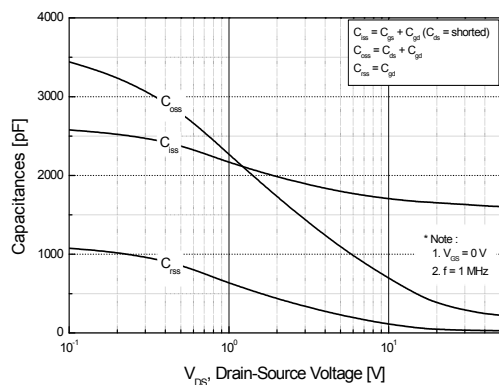
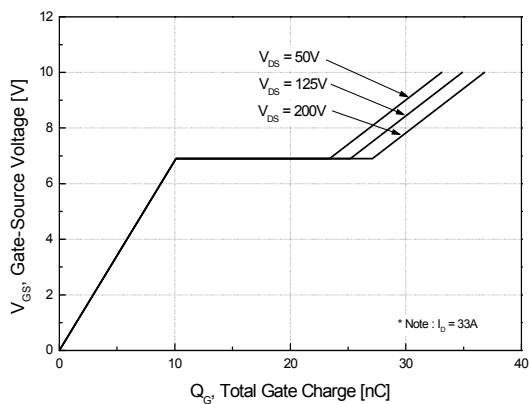


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

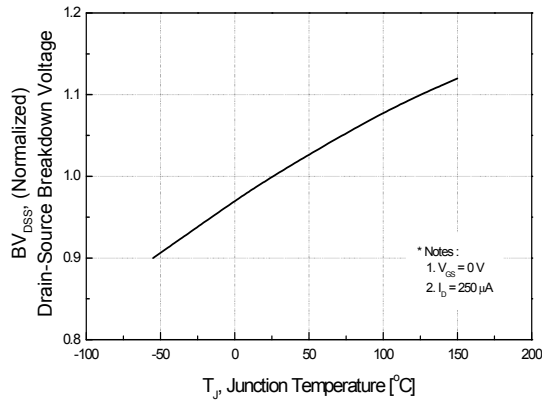


Figure 8. On-Resistance Variation vs. Temperature

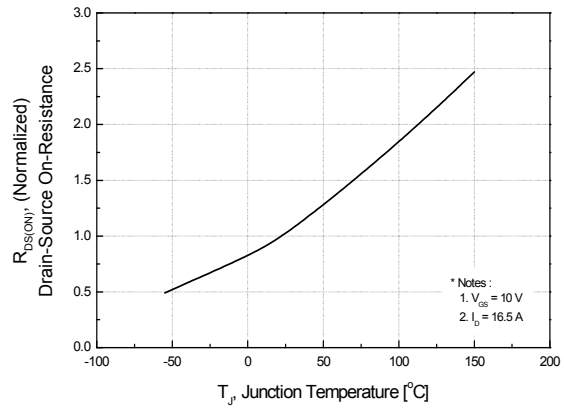


Figure 9. Maximum Safe Operating Area

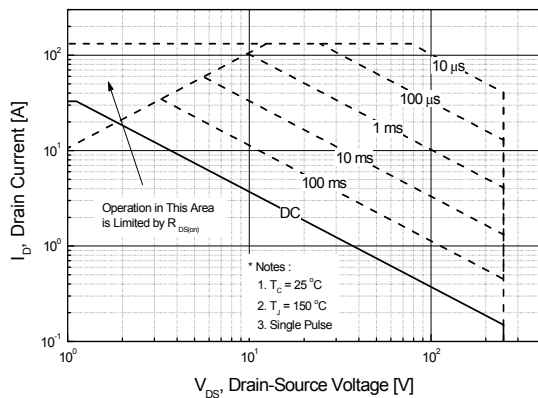


Figure 10. Maximum Drain Current vs. Case Temperature

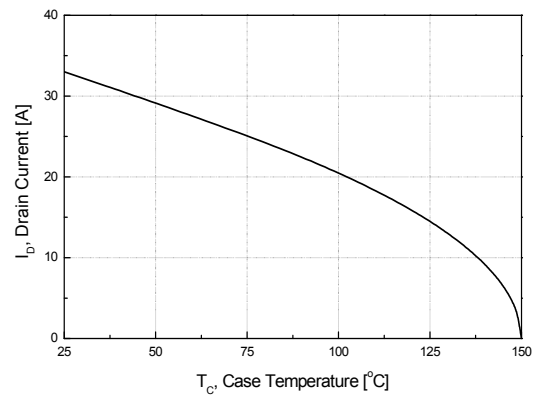
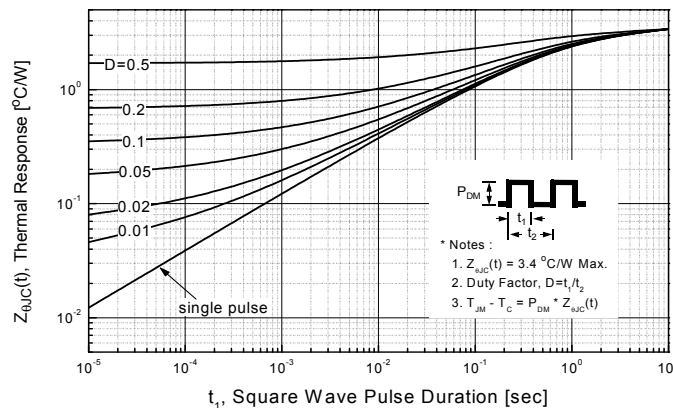


Figure 11. Transient Thermal Response Curve



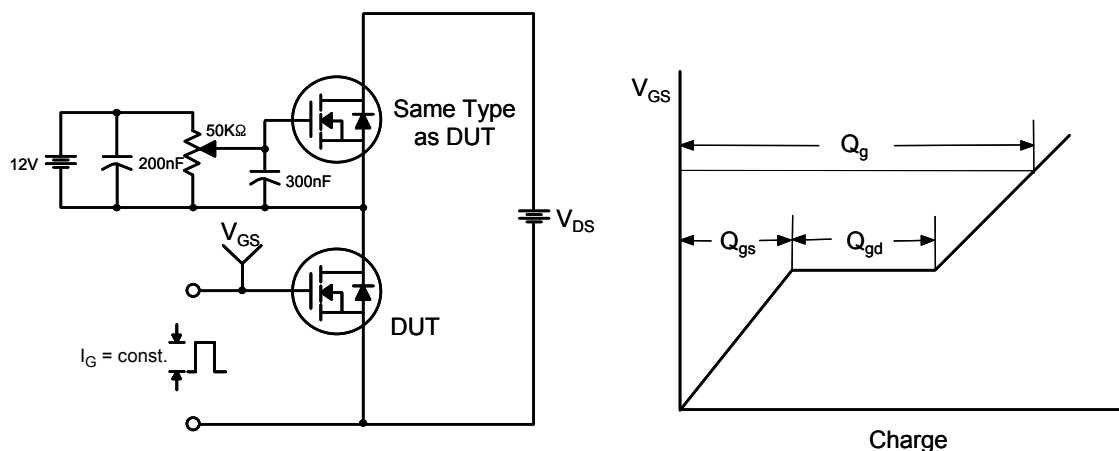


Figure 12. Gate Charge Test Circuit & Waveform

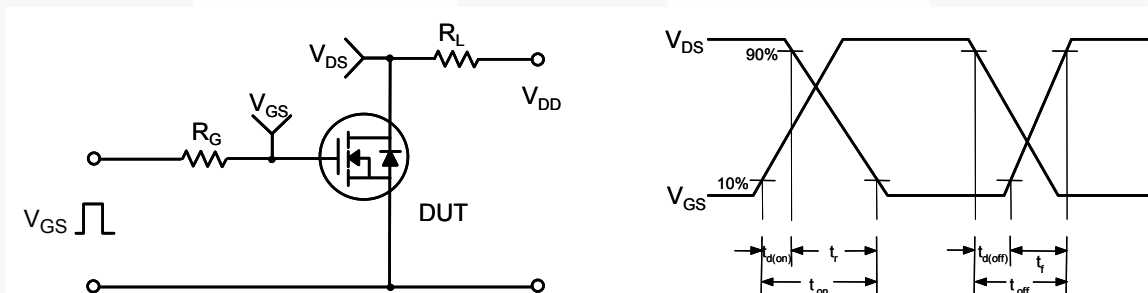


Figure 13. Resistive Switching Test Circuit & Waveforms

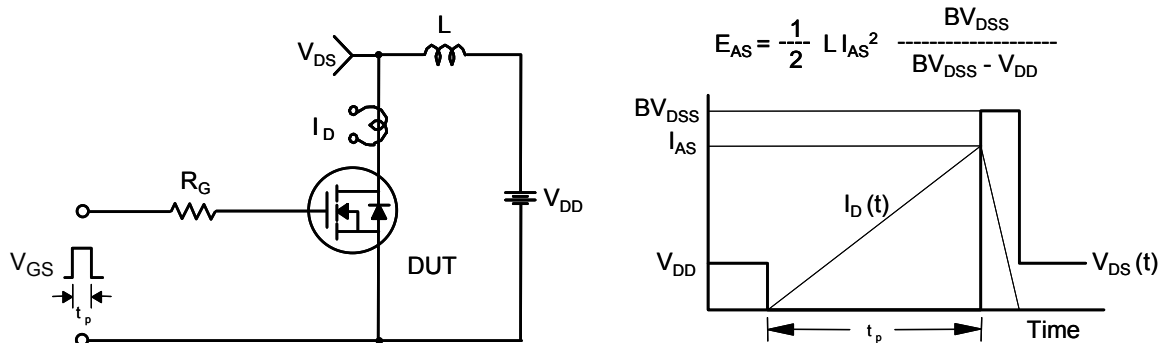


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

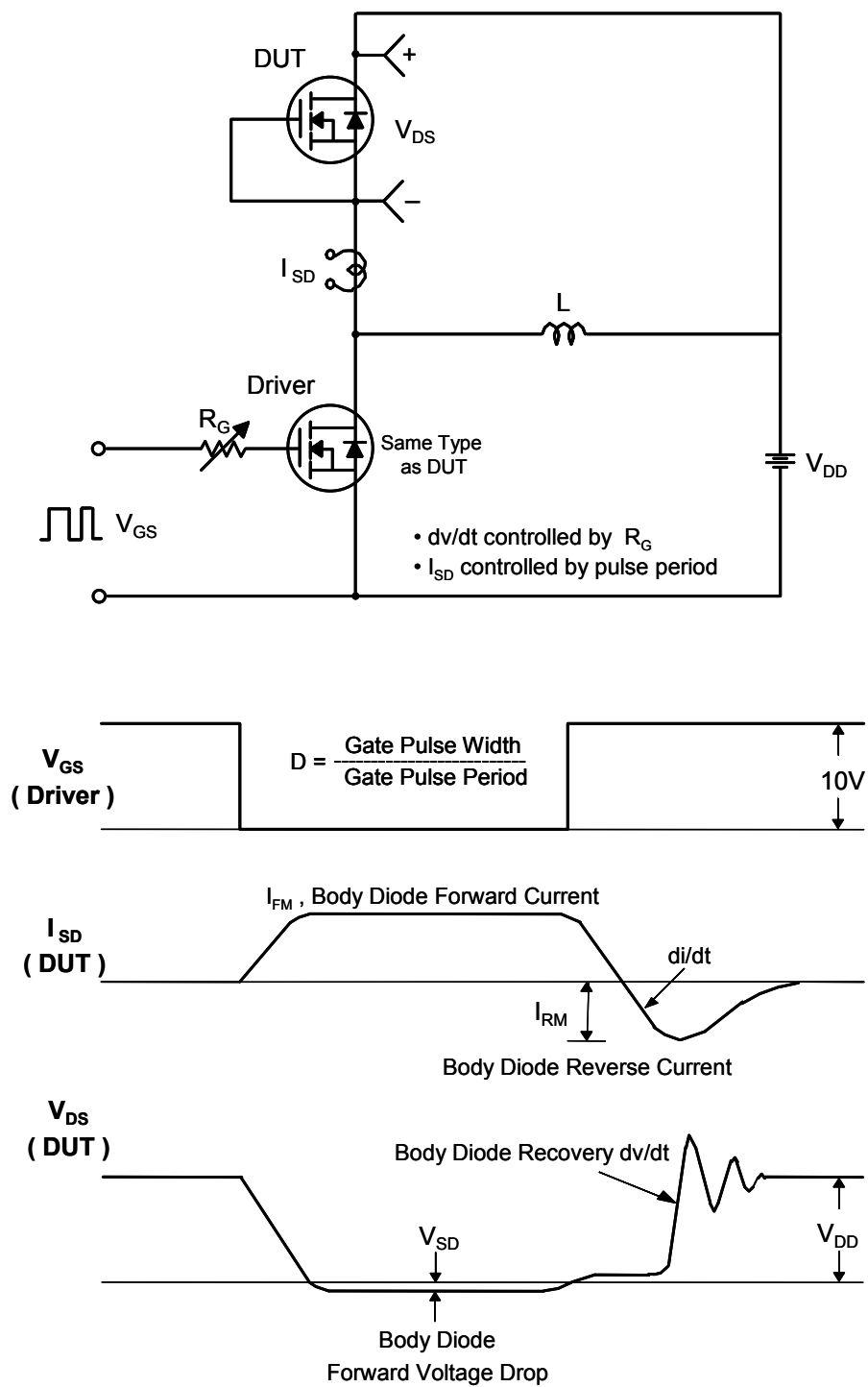
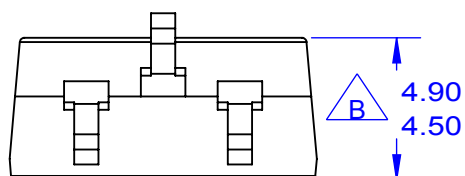
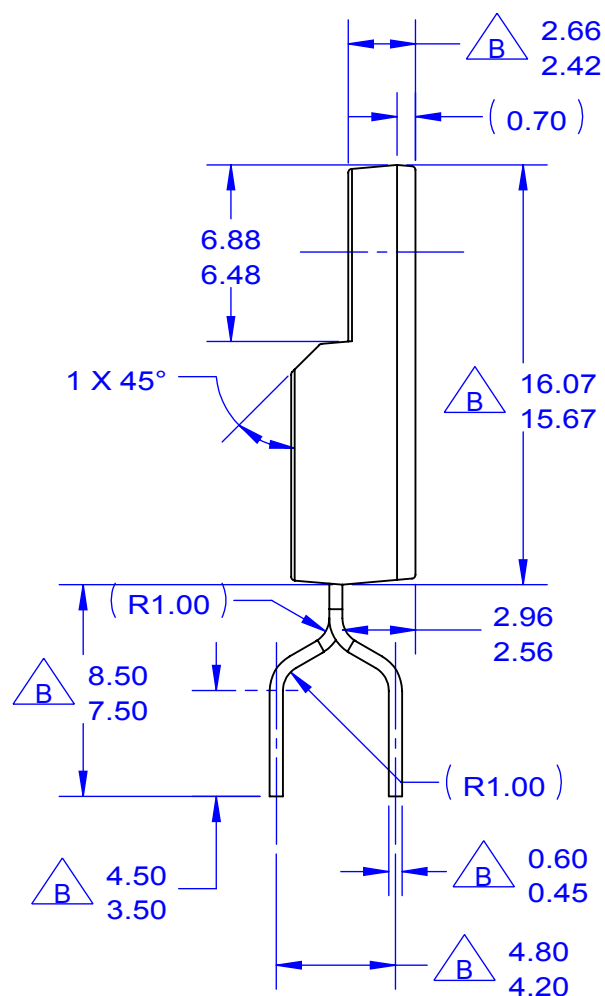
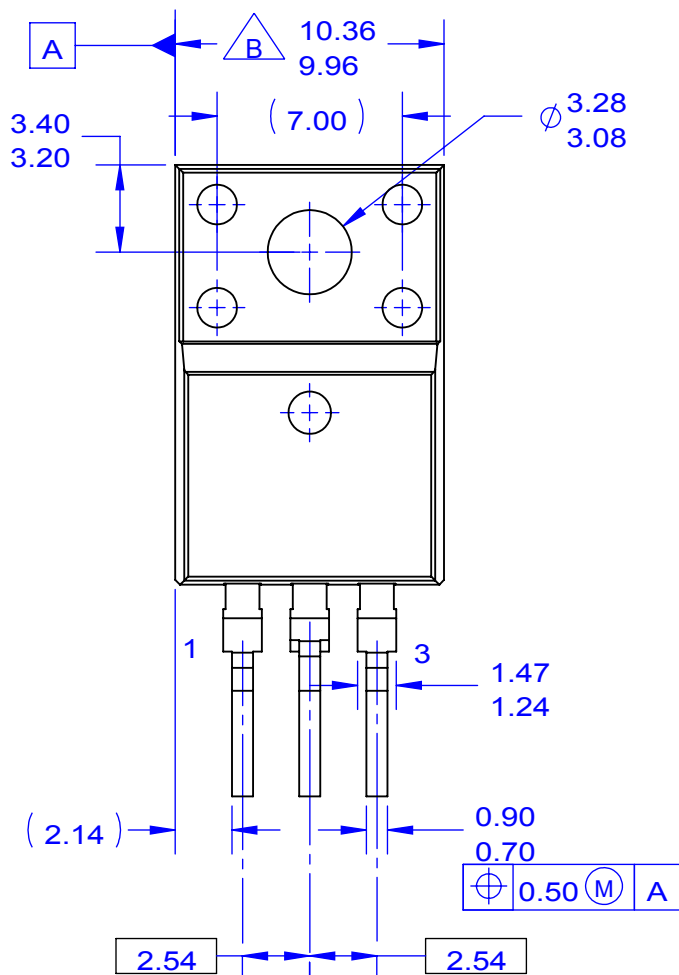


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

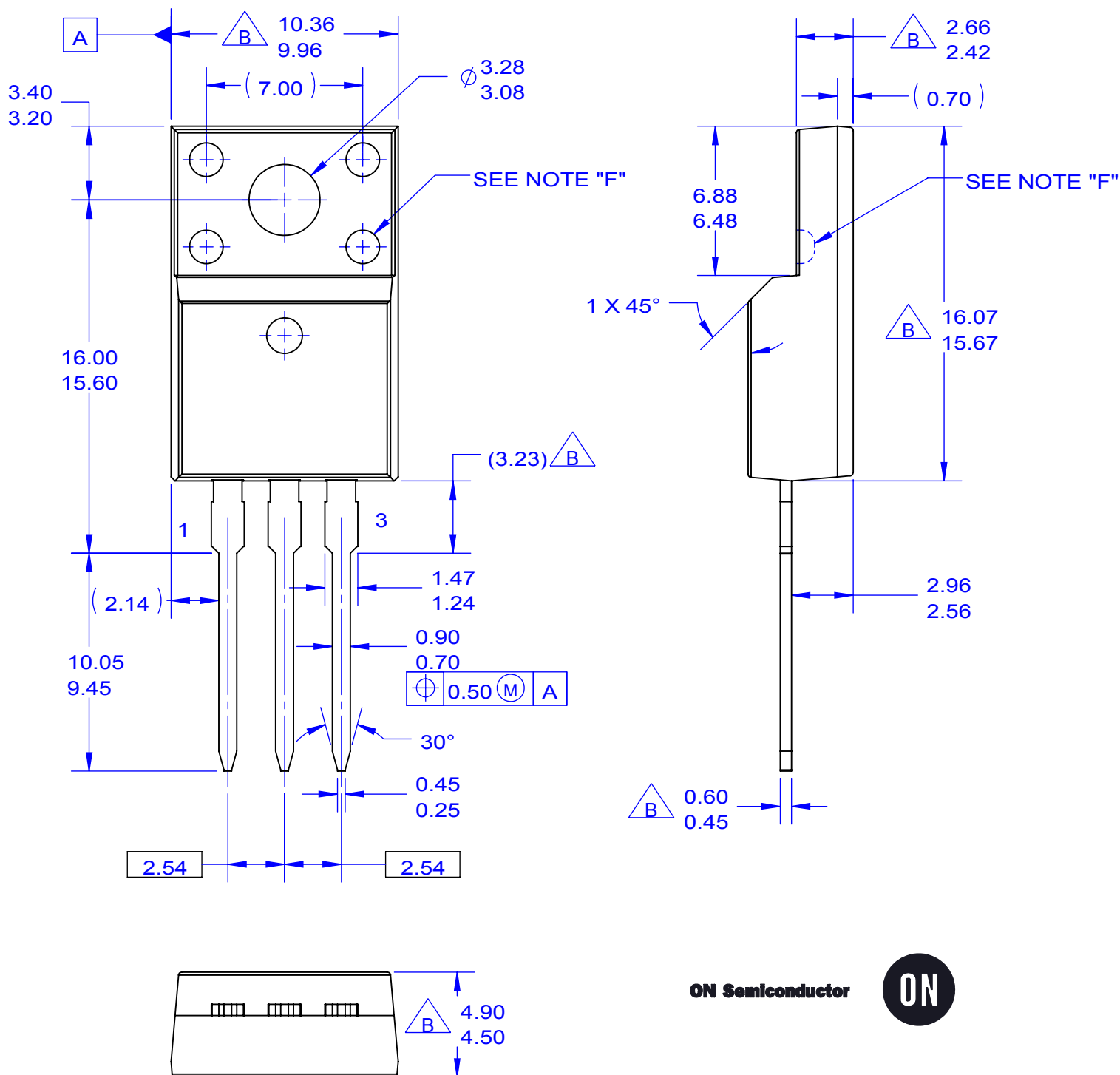


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NOTES:

- EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- DOES NOT COMPLY EIAJ STD. VALUE.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
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